

Quadrant Si PIN Photo Diode

Characteristics:

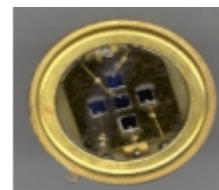
Planar Front Incident Structure.

Fast Response.

Low Dark Current.

High Responsivity.

High Reliability.



Applications:

Opto-Electronic Target Detecting System

0.4-1.1 μ m Light Detection And OE ConveIPion System

Physical and Chemical Process Optical Detecting

Mechanism

The device works like reveIPe biased diode array, since the device is configured as quadrature, when the light form the tested object strike equally upon each quadrant, the light current from quadrants should be equal. When the tested object position changed, the output of each quadrant will change. So the direction of the target can determined.

Technical Parameter(TA=23℃)

Parameter		Symbol	Test Conditions	Least Value	Typical Value	Most Value	Unit
Active Area		Φ			1×1×5		mm ²
Optical Parameter	Spectrum Response Range	λ			400~1100		nm
	Responsivity	Re	V _R =15V λ =550nm	0.1			μ A/ μ W
	Rising time	tr	V _R =15V		5.5	6.0	nS
Electrical Parameter	Dark Current	I _D	V _R =15V		3	10	nA
	Resistivity between Polarity	V _{BR}	I _R =10 μ A	30			V
	Capacitance	C _j	f=1MHz V _R =15V		4	8	pF

Typical Operating Characteristics

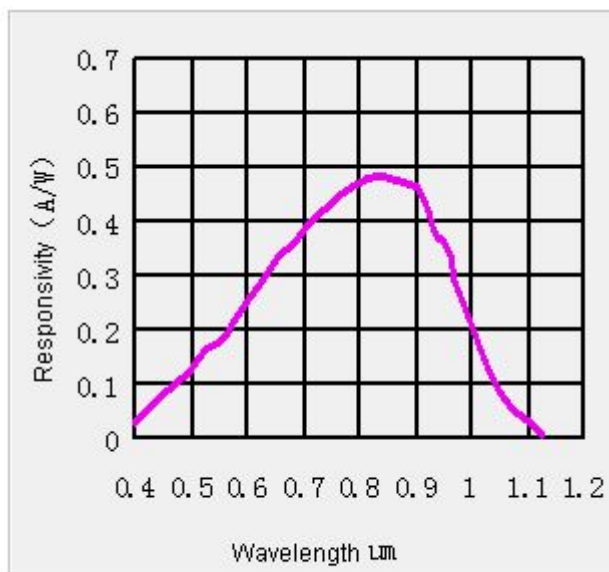
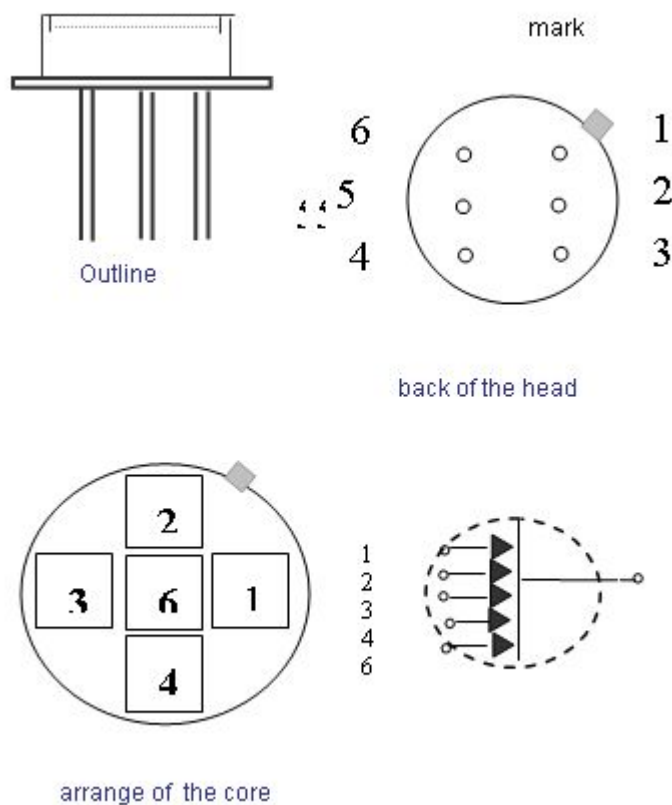


Fig. 1 Spectrum response curve

Package Information and Lead connection (Lead turn named by back side view)



Note :

ReveIpe Bias ;No Vibration and shock when device operating;Static Charge Protection (Storage, Operating)